

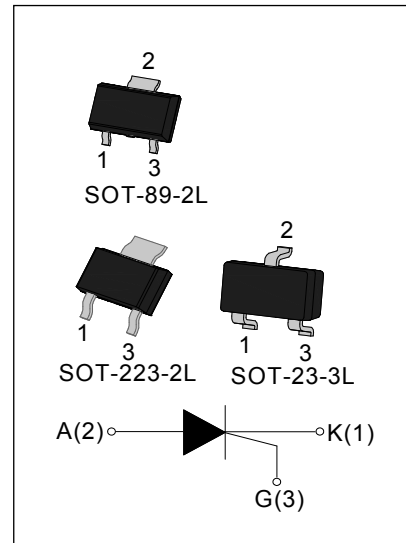


### DESCRIPTION:

The JX008 SCR series provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc. All the packages mentioned are RoHS compliant. (2011/65/EU)

### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
$I_{GT}$	$\leq 200$	$\mu A$



### ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40-150	$^{\circ}C$
Operating junction temperature range		$T_j$	-40-125 <sup>①</sup>	$^{\circ}C$
Repetitive peak off-state voltage		$V_{DRM}$	600	V
Repetitive peak reverse voltage		$V_{RRM}$	600	V
RMS on-state current	SOT-23-3L ( $T_c=40^{\circ}C$ )	$I_{T(RMS)}$	0.8	A
	SOT-89-2L ( $T_c=70^{\circ}C$ )			
	SOT-223-2L ( $T_c=90^{\circ}C$ )			
Non repetitive surge peak on-state current (F=50Hz $t_p=10ms$ )		$I_{TSM}$	8	A
Non repetitive surge peak on-state current (F=60Hz $t_p=8.3ms$ )		$I_{TSM}$	9	A
$I^2t$ value for fusing ( $t_p=10ms$ )		$I^2t$	0.32	$A^2s$
Critical rate of rise of on-state current		$di/dt$	50	$A/\mu s$
Peak gate current ( $t_p=20\mu s$ , $T_j=125^{\circ}C$ )		$I_{GM}$	0.2	A
Peak gate power ( $t_p=20\mu s$ , $T_j=125^{\circ}C$ )		$P_{GM}$	0.5	W
Average gate power dissipation ( $T_j=125^{\circ}C$ )		$P_{G(AV)}$	0.1	W

**NOTE 1:** When we parallel connect a  $\leq 1K\Omega$  resistor between Gate and Cathode, the  $T_j$  can reach  $125^{\circ}C$ ; if without this resistor, the  $T_j$  only can reach  $110^{\circ}C$ .

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12\text{V } R_L=33\Omega$	20	50	200	$\mu\text{A}$
$V_{GT}$		-	0.6	0.8	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$	0.2	-	-	V
$I_L$	$I_G=1.2 I_{GT}$	-	-	4	mA
$I_H$	$I_T=0.05\text{A}$	-	-	3	mA
dV/dt	$V_D=400\text{V } T_j=125^{\circ}\text{C } R_{GK}=1\text{K}\Omega$	600	-	-	V/ $\mu\text{s}$
dV/dt	$V_D=400\text{V } T_j=125^{\circ}\text{C } R_{GK}=220\Omega$	1000	-	-	V/ $\mu\text{s}$
$t_{on}$	$I_G=10\text{mA } I_A=4\text{mA } I_R=0.4\text{mA}$ $T_j=25^{\circ}\text{C}$	-	2	-	$\mu\text{s}$
$t_{off}$		-	50	-	$\mu\text{s}$
$R_d$	Dynamic Resistance $T_j=125^{\circ}\text{C}$	-	-	35	m $\Omega$

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_T=1.1\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^{\circ}\text{C}$	100	$\mu\text{A}$

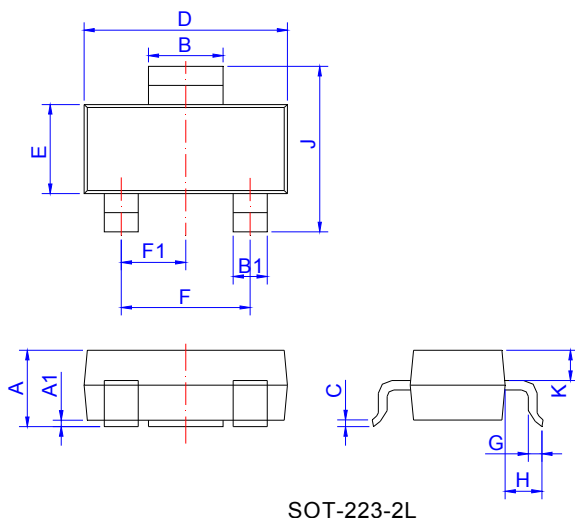
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	SOT-23-3L	75	$^{\circ}\text{C/W}$
		SOT-89-2L	45	
		SOT-223-2L	31	
$R_{th(j-a)}$	junction to ambient	SOT-23-3L	125	$^{\circ}\text{C/W}$
		SOT-89-2L	90	
		SOT-223-2L	60	

**ORDERING INFORMATION**

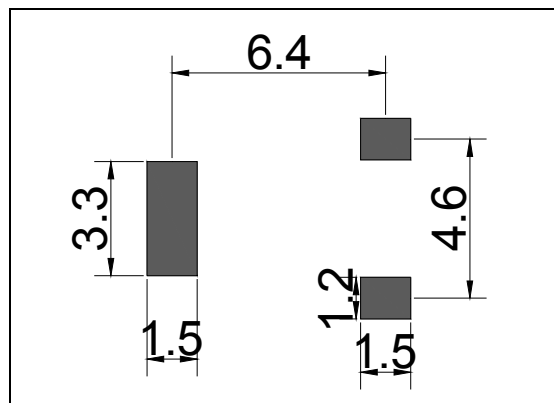
<p><b>J</b></p> <p>JieJie Microelectronics Co.,Ltd</p> <p>Sensitive gate SCRs</p>	<p><b>X</b></p>	<p><b>008</b></p> <p><math>I_{T(RMS)}:0.8A</math></p>	<p><b>W</b></p> <p>L:SOT-23-3L N2:SOT-89-2L W:SOT-223-2L</p>
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**PACKAGE MECHANICAL DATA**

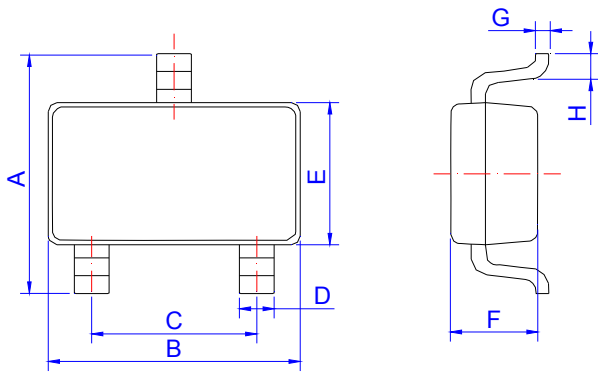


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
H	1.5	1.75	2	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K		0.9			0.035	

**FOOTPRINT-SOT-223-2L (dimensions in mm)**



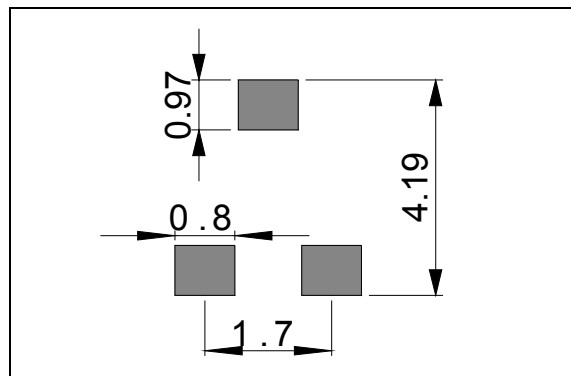
**PACKAGE MECHANICAL DATA**



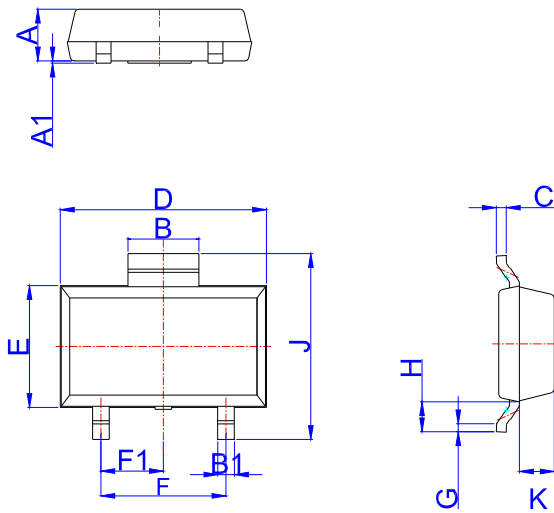
SOT-23-3L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.65	2.80	2.95	0.104	0.110	0.116
B	2.82	2.92	3.02	0.111	0.115	0.119
C	1.80	1.90	2.00	0.071	0.075	0.079
D	0.30	0.35	0.50	0.012	0.014	0.020
E	1.50	1.60	1.70	0.059	0.063	0.067
F	1.07	1.17	1.27	0.042	0.046	0.050
G	0.05	0.15	0.25	0.002	0.006	0.010
H	0.25	0.40	0.55	0.010	0.016	0.022

**FOOTPRINT-SOT-23-3L (dimensions in mm)**



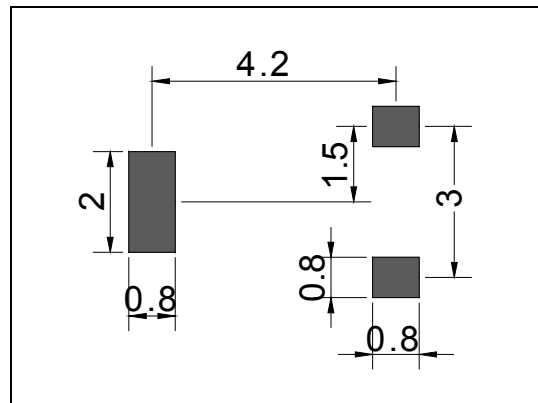
PACKAGE MECHANICAL DATA



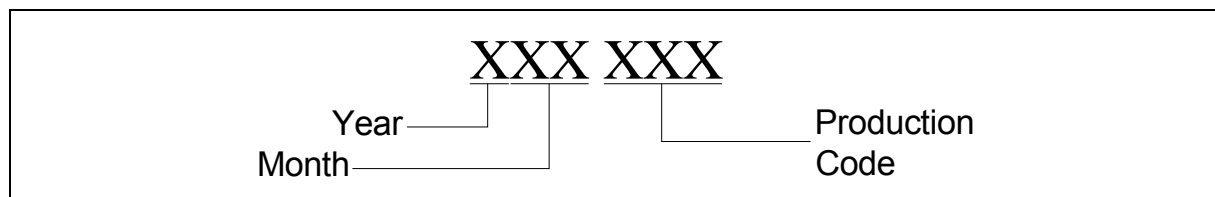
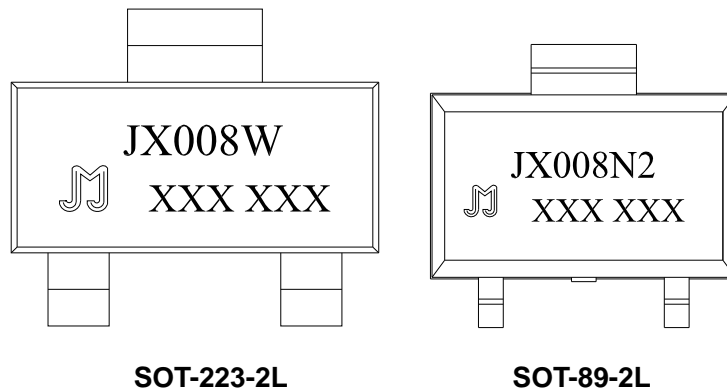
SOT-89-2L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.3	1.4	1.5	0.051	0.055	0.059
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	1.6	1.7	1.8	0.063	0.067	0.071
B1	0.3	0.4	0.5	0.012	0.016	0.020
C	0.22	0.254	0.32	0.009	0.010	0.013
D	4.75	4.95	5.15	0.187	0.195	0.203
E	2.75	2.95	3.15	0.108	0.116	0.124
F		3.0			0.118	
F1		1.5			0.059	
G	0.2	0.3	0.4	0.008	0.012	0.016
H	0.58	0.78	0.98	0.023	0.031	0.039
J	4.3	4.5	4.7	0.169	0.177	0.185
K		0.88			0.035	

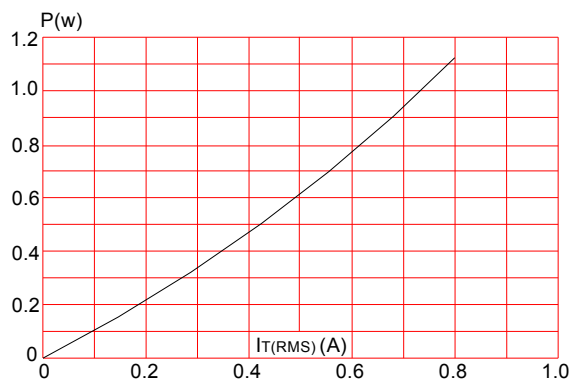
FOOTPRINT-SOT-89-2L (dimensions in mm)



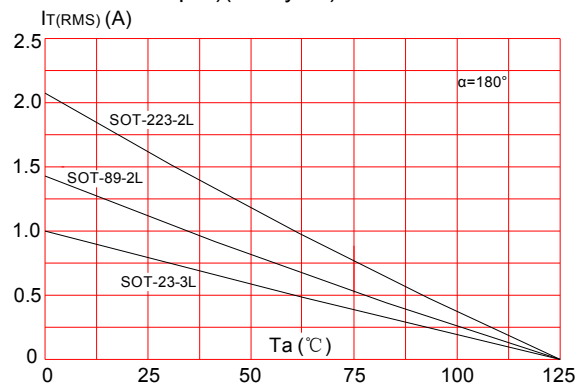
MARKING



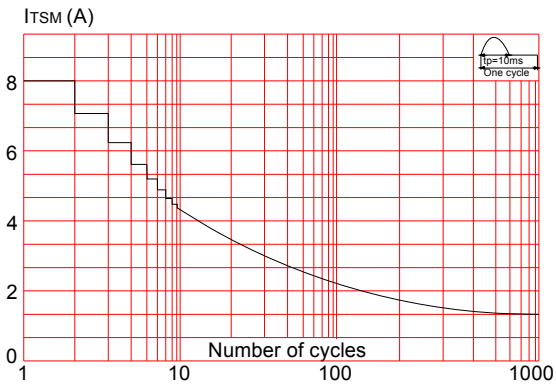
**FIG.1** Maximum power dissipation versus RMS on-state current



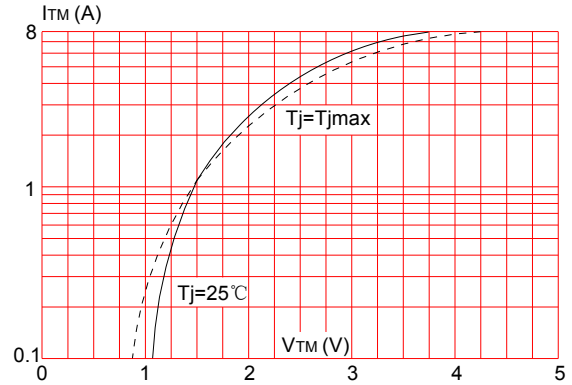
**FIG.2:** RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35μm)(full cycle)



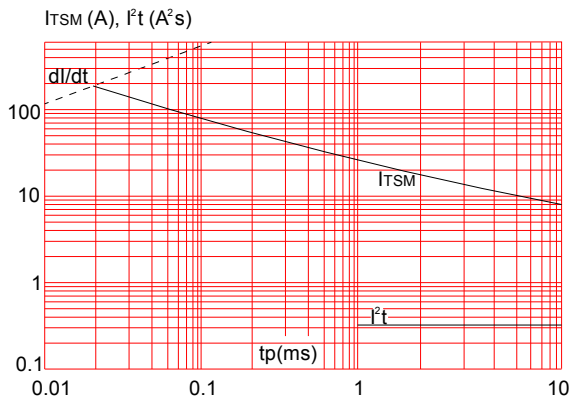
**FIG.3:** Surge peak on-state current versus number of cycles



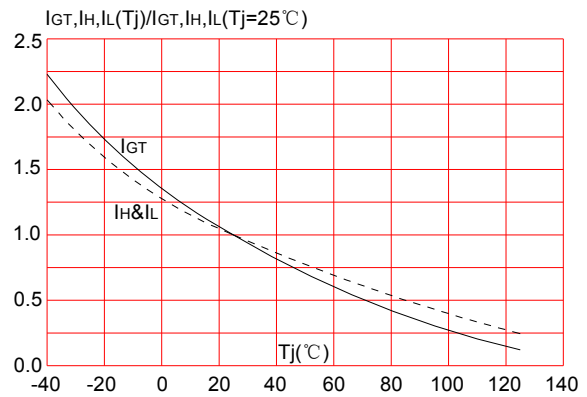
**FIG.4:** On-state characteristics (maximum values)



**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 50\text{A}/\mu\text{s}$ )

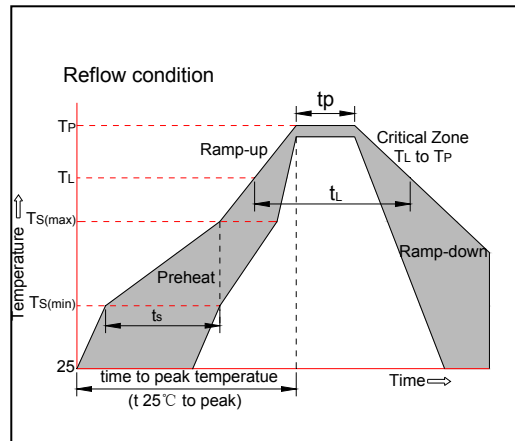


**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature




**SOLDERING PARAMETERS**

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150°C
	-Temperature Max ( $T_{s(max)}$ )	+200°C
	-Time (Min to Max) ( $t_s$ )	60-180 secs.
Average ramp up rate (Liquidus Temp ( $T_L$ ) to peak)		3°C/sec. Max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature( $T_L$ ) (Liquidus)	+217°C
	-Temperature( $t_L$ )	60-150 secs.
Peak Temp ( $T_p$ )		+260(+0/-5)°C
Time within 5°C of actual Peak Temp ( $t_p$ )		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp ( $T_P$ )		8 min. Max
Do not exceed		+260°C



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